

NTD20P06L

Power MOSFET

-60 V, -15.5 A, Single P-Channel, DPAK

Features

- Withstands High Energy in Avalanche and Commutation Modes
- Low Gate Charge for Fast Switching
- Pb-Free Packages are Available

Applications

- Bridge Circuits
- Power Supplies, Power Motor Controls
- DC-DC Conversion

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Value	Unit	
Drain-to-Source Voltage	V _{DSS}	-60	V	
Gate-to-Source Voltage	Continuous	V _{GS}	± 20 V	
	Non-Repetitive	t _p ≤ 10 ms	V _{GSM}	± 30
Continuous Drain Current (Note 1)	Steady State	T _A = 25°C	I _D	-15.5 A
	Steady State	T _A = 25°C	P _D	65 W
Pulsed Drain Current	t _p = 10 μs	I _{DM}	± 50 A	
Operating Junction and Storage Temperature		T _J , T _{STG}	-55 to 175	°C
Single Pulse Drain-to-Source Avalanche Energy (V _{DD} = 25 V, V _{GS} = 5 V, I _{PK} = 15 A, L = 2.7 mH, R _G = 25 Ω)		E _{AS}	304	mJ
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)		T _L	260	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Case (Drain)	R _{θJC}	2.3	°C/W
Junction-to-Ambient - Steady State (Note 1)	R _{θJA}	80	
Junction-to-Ambient - Steady State (Note 2)	R _{θJA}	110	

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. Surface-mounted on FR4 board using 1 in sq. pad size (Cu area = 1.127 in sq. [1 oz] including traces)
2. Surface-mounted on FR4 board using the minimum recommended pad size (Cu area = 0.412 in sq.)

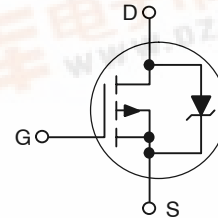


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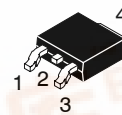
<http://onsemi.com>

V _{(BR)DSS}	R _{DS(on)} TYP	I _D MAX (Note 1)
-60 V	130 mΩ @ -5.0 V	-15.5 A

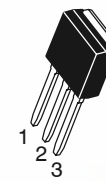
P-Channel



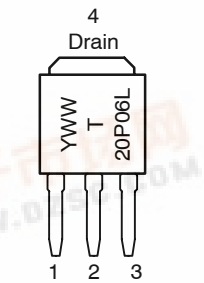
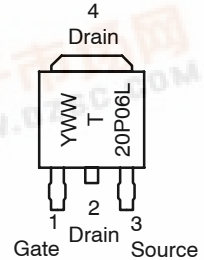
MARKING DIAGRAMS



DPAK
CASE 369C
Style 2



DPAK
CASE 369D
Style 2



20P06L Device Code
Y = Year
WW = Work Week

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.



NTD20P06L

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Units
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = -250 μA	-60	-74		V	
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J			-64		mV/°C	
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = -60 V	T _J = 25°C			-1.0	μA
			T _J = 150°C			-10	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA	

ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = -250 μA	-1.0	-1.5	-2.0	V	
Gate Threshold Temperature Coefficient	V _{GS(TH)} /T _J			3.1		mV/°C	
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = -5.0 V, I _D = -7.5 A		0.130	0.150	Ω	
		V _{GS} = -5.0 V, I _D = -15 A		0.143			
Forward Transconductance	g _{FS}	V _{DS} = -10 V, I _D = -7.5 A		11		S	
Drain-to-Source On-Voltage	V _{DS(on)}	V _{GS} = -5.0 V, I _D = -7.5 A	T _J = 25°C			-1.2	V
			T _J = 150°C			-1.9	

CHARGES AND CAPACITANCES

Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1 MHz, V _{DS} = -25 V		740	1190	pF
Output Capacitance	C _{OSS}			207	300	
Reverse Transfer Capacitance	C _{RSS}			66	120	
Total Gate Charge	Q _{G(TOT)}	V _{GS} = -5.0 V, V _{DS} = -48 V, I _D = -18 A		15	26	nC
Gate-to-Source Charge	Q _{GS}			4.0		
Gate-to-Drain Charge	Q _{GD}			7.0		

SWITCHING CHARACTERISTICS (Note 4)

Turn-On Delay Time	t _{d(ON)}	V _{GS} = -5.0 V, V _{DD} = -30 V, I _D = -15 A, R _G = 9.1 Ω		11	20	ns
Rise Time	t _r			90	180	
Turn-Off Delay Time	t _{d(OFF)}			28	50	
Fall Time	t _f			70	135	

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = -15 A	T _J = 25°C		1.5	2.5	V
			T _J = 150°C		1.3		
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, d _{IS} /d _t = 100 A/μs, I _S = -12 A		60		ns	
Charge Time	t _a			39			
Discharge Time	t _b			21			
Reverse Recovery Charge	Q _{RR}			0.13			nC

3. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%

4. Switching characteristics are independent of operating junction temperatures

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TYPICAL PERFORMANCE CURVES

($T_J = 25^\circ\text{C}$ unless otherwise noted)

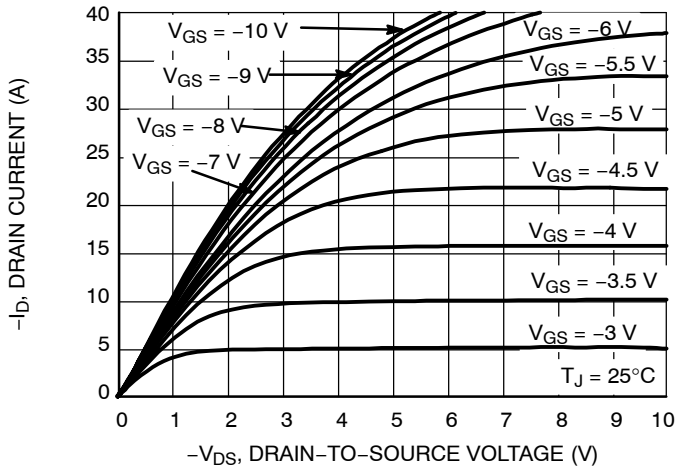


Figure 1. On-Region Characteristics

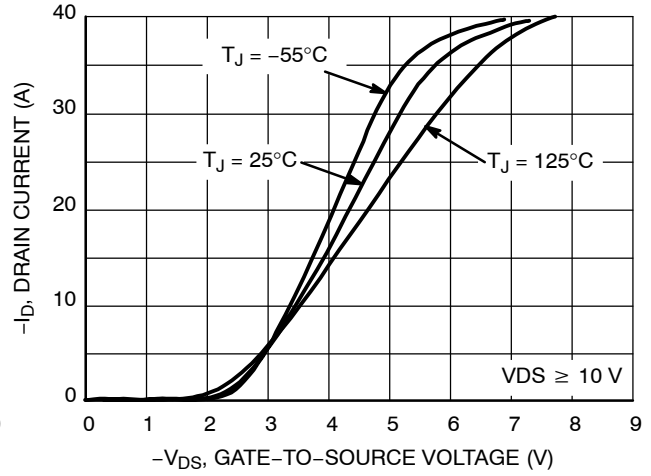


Figure 2. Transfer Characteristics

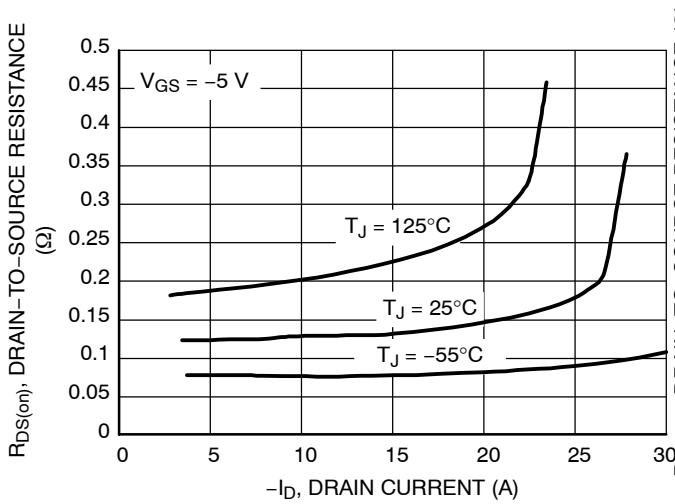


Figure 3. On-Resistance versus Drain Current and Temperature

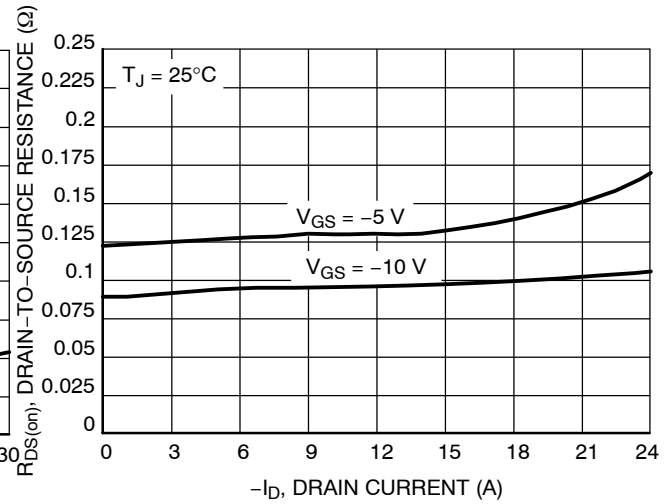


Figure 4. On-Resistance versus Drain Current and Gate Voltage

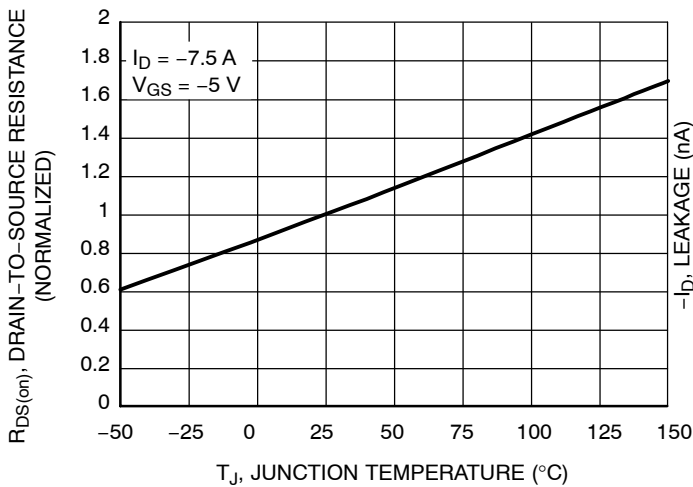


Figure 5. On-Resistance Variation with Temperature

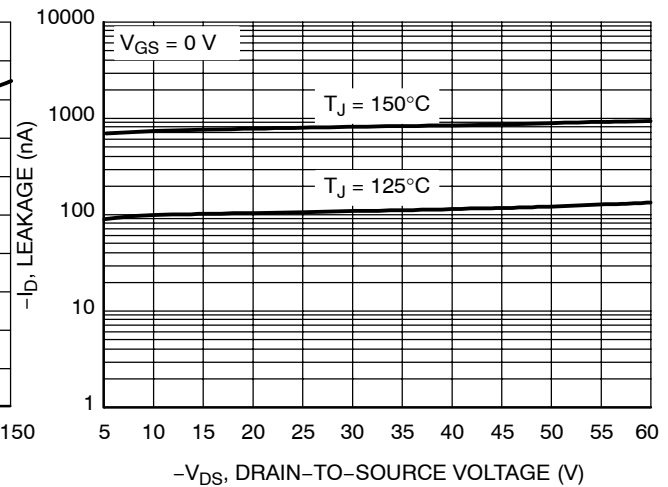


Figure 6. Drain-to-Source Leakage Current versus Voltage

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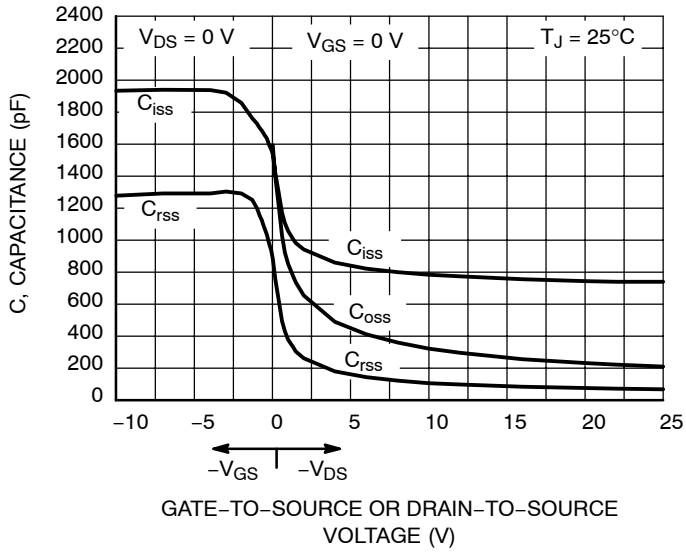


Figure 7. Capacitance Variation

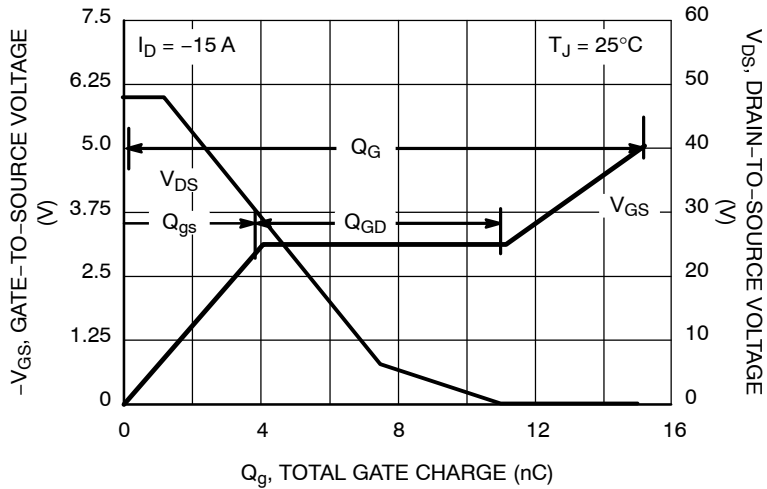


Figure 8. Gate-to-Source and Drain-to-Source Voltage versus Total Charge

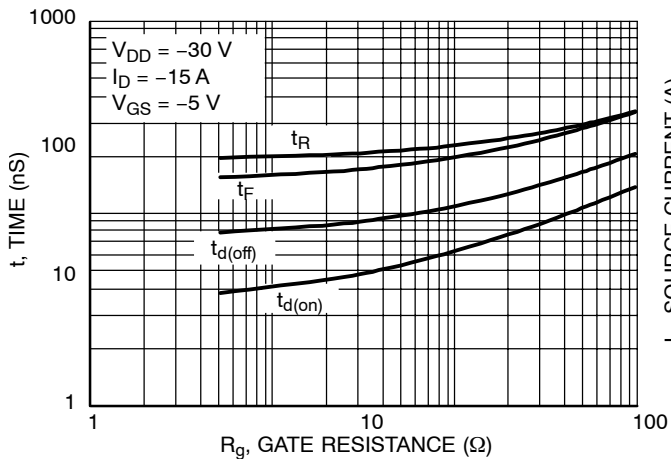


Figure 9. Resistive Switching Time Variation versus Gate Resistance

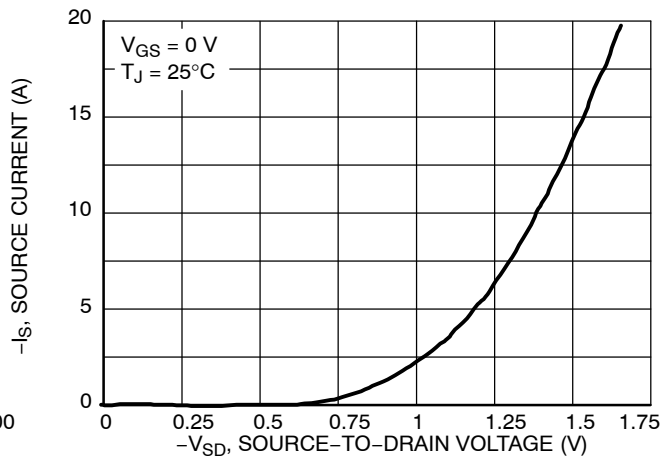


Figure 10. Diode Forward Voltage versus Current

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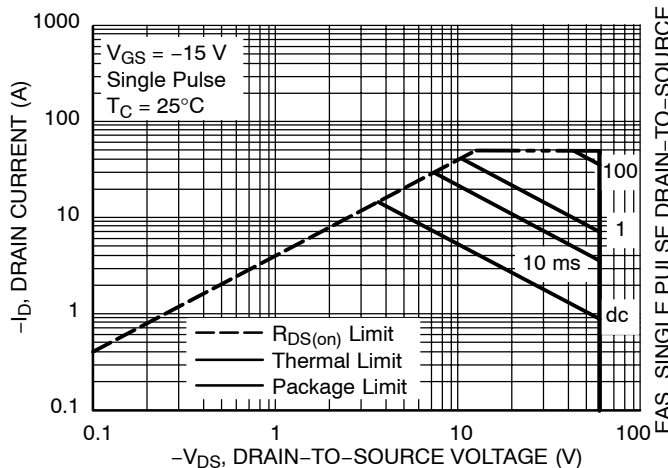


Figure 11. Maximum Rated Forward Biased Safe Operating Area

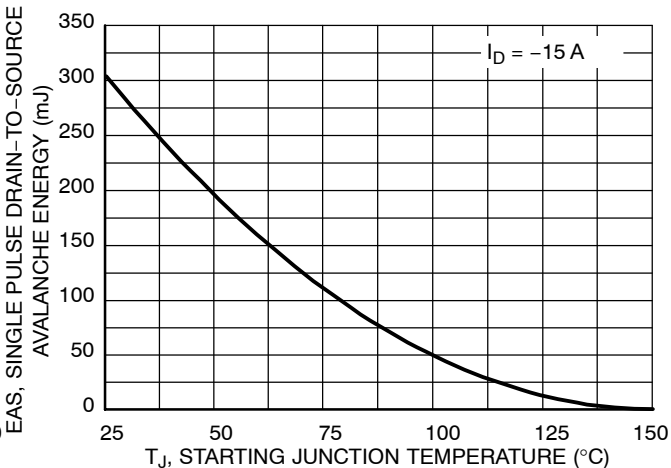


Figure 12. Maximum Avalanche Energy versus Starting Junction Temperature

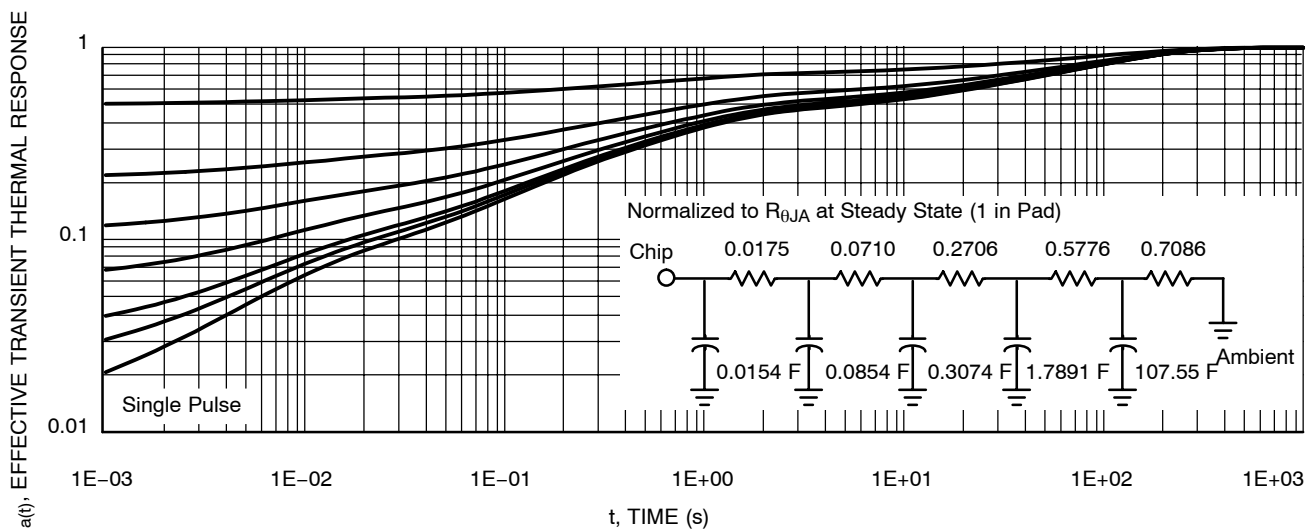


Figure 13. Thermal Response

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ORDERING INFORMATION

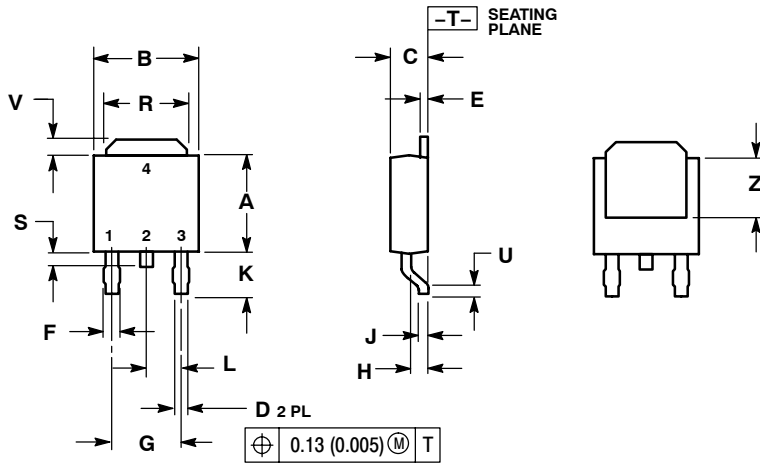
Device	Package	Shipping [†]
NTD20P06L-1	DPAK	75 Units / Rail
NTD20P06L		75 Units / Rail
NTD20P06LT4		2500 /Tape & Reel
NTD20P06L-1G	DPAK (Pb-Free)	75 Units / Rail
NTD20P06LG		75 Units / Rail
NTD20P06LT4G		2500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NTD20P06L

PACKAGE DIMENSIONS

DPAK-3
CASE 369C-01
ISSUE O

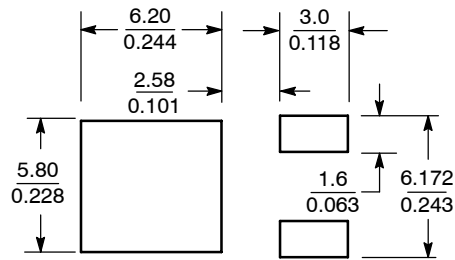


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.22
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.180 BSC		4.58 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.102	0.114	2.60	2.89
L	0.090 BSC		2.29 BSC	
R	0.180	0.215	4.57	5.45
S	0.025	0.040	0.63	1.01
U	0.020	---	0.51	---
V	0.035	0.050	0.89	1.27
Z	0.155	---	3.93	---

- STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

SOLDERING FOOTPRINT*



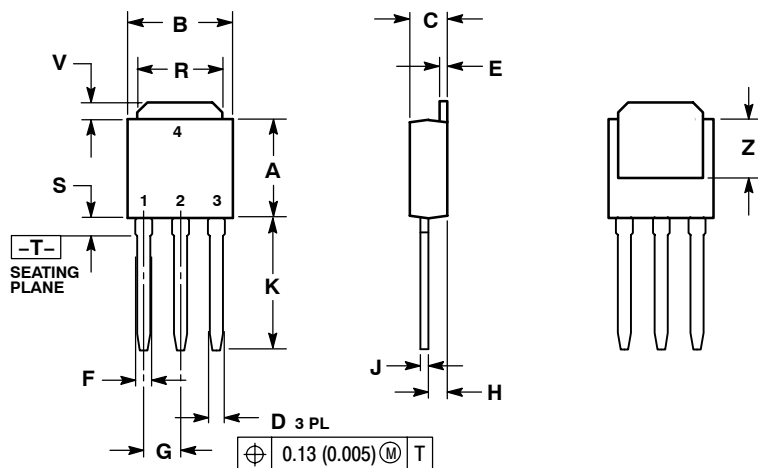
SCALE 3:1 $\left(\frac{\text{mm}}{\text{inches}} \right)$

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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PACKAGE DIMENSIONS

DPAK-3
CASE 369D-01
ISSUE B



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.35
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090 BSC		2.29 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
V	0.035	0.050	0.89	1.27
Z	0.155	---	3.93	---

- STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

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